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(54) **METHOD OF PRODUCING P-DOPED SILICON SINGLE CRYSTAL AND P-DOPED N-TYPE SILICON SINGLE CRYSTAL WAFER**

VERFAHREN ZUR HERSTELLUNG EINES SILIKON-EINZELKRISTALLS MIT P-ZUSATZ UND
EINES SILIKON-EINZELKRISTALL-WAFERS MIT P-ZUSATZ DES TYPUS N

PROCEDE DE PRODUCTION D'UN MONOCRISTAL DE SILICIUM A DOPAGE P ET TRANCHE A
MONOCRISTAL DE SILICIUM A DOPAGE P ET DE TYPE N

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